



Monolithic N-Channel JFET Dual

PRODUCT SUMMARY				
$V_{GS(off)}$ (V)	$V_{(BR)GSS}$ Min (V)	g_{fs} Min (mS)	I_G Max (pA)	$ V_{GS1} - V_{GS2} $ Max (mV)
-1.0 to -4.5	-50	1	-50	25

FEATURES

- Monolithic Design
- High Slew Rate
- Low Offset/Drift Voltage
- Low Gate Leakage: 5 pA
- Low Noise: 9 nV/√Hz
- High CMRR: 100 dB

BENEFITS

- Tight Differential Match vs. Current
- Improved Op Amp Speed, Settling Time Accuracy
- Minimum Input Error/Trimming Requirement
- Insignificant Signal Loss/Error Voltage
- High System Sensitivity
- Minimum Error with Large Input Signal

APPLICATIONS

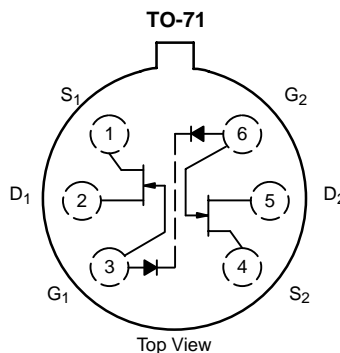
- Wideband Differential Amps
- High-Speed, Temp-Compensated, Single-Ended Input Amps
- High Speed Comparators
- Impedance Converters

DESCRIPTION

The low cost 2N3958 JFET dual is designed for high-performance differential amplification for a wide range of precision test instrumentation applications. This series features tightly matched specs, low gate leakage for accuracy, and wide dynamic range with I_G guaranteed at $V_{DG} = 20$ V.

The hermetically-sealed TO-71 package is available with full military processing (see Military Information and the 2N5545/5546/5547JANTX/JANTXV data sheet).

For similar products see 2N5196/5197/5198/5199, the low-noise U/SST401 series, the high-gain 2N5911/5912, and the low-leakage U421/423 data sheets.



ABSOLUTE MAXIMUM RATINGS

Gate-Drain, Gate-Source Voltage -50 V
 Gate Current 50 mA
 Lead Temperature ($1/16$ " from case for 10 sec.) 300 °C
 Storage Temperature -65 to 200 °C
 Operating Junction Temperature -55 to 150 °C

Power Dissipation : Per Side^a 250 mW
 Total^b 500 mW

Notes
 a. Derate 2 mW/°C above 85 °C
 b. Derate 4 mW/°C above 85 °C

SPECIFICATIONS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min	Typ ^a	Max	
Static						
Gate-Source Breakdown Voltage	$V_{(BR)GSS}$	$I_G = -1\ \mu\text{A}$, $V_{DS} = 0\ \text{V}$	-50	-57		V
Gate-Source Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = 20\ \text{V}$, $I_D = 1\ \text{nA}$	-1.0	-2	-4.5	
Saturation Drain Current ^b	I_{DSS}	$V_{DS} = 20\ \text{V}$, $V_{GS} = 0\ \text{V}$	0.5	3	5	mA
Gate Reverse Current	I_{GSS}	$V_{GS} = -30\ \text{V}$, $V_{DS} = 0\ \text{V}$		-10	-100	pA
		$T_A = 150^\circ\text{C}$		-20	-500	nA
Gate Operating Current	I_G	$V_{DG} = 20\ \text{V}$, $I_D = 200\ \mu\text{A}$		-5	-50	pA
		$T_A = 125^\circ\text{C}$		-0.8	-250	nA
Gate-Source Voltage	V_{GS}	$V_{DG} = 20\ \text{V}$, $I_D = 200\ \mu\text{A}$	-0.5	-1.5	-4	V
		$I_D = 50\ \mu\text{A}$			-4.2	
Gate-Source Forward Voltage	$V_{GS(F)}$	$I_G = 1\ \text{mA}$, $V_{DS} = 0\ \text{V}$			2	
Dynamic						
Common-Source Forward Transconductance	g_{fs}	$V_{DS} = 20\ \text{V}$, $V_{GS} = 0\ \text{V}$ $f = 1\ \text{kHz}$	1	2.5	3	mS
Common-Source Output Conductance	g_{os}			2	35	μS
Common-Source Input Capacitance	C_{iss}	$V_{DS} = 20\ \text{V}$, $V_{GS} = 0\ \text{V}$ $f = 1\ \text{MHz}$		3	4	pF
Common-Source Reverse Transfer Capacitance	C_{rss}			1	1.2	
Drain-Gate Capacitance	C_{dg}	$V_{DG} = 10\ \text{V}$, $I_S = 0$, $f = 1\ \text{MHz}$			1.5	
Equivalent Input Noise Voltage	\bar{e}_n	$V_{DS} = 20\ \text{V}$, $V_{GS} = 0\ \text{V}$, $f = 1\ \text{kHz}$		9		$\text{nV}/\sqrt{\text{Hz}}$
Noise Figure	NF	$V_{DS} = 20\ \text{V}$, $V_{GS} = 0\ \text{V}$ $f = 100\ \text{Hz}$, $R_G = 10\ \text{M}\Omega$			0.5	dB
Matching						
Differential Gate-Source Voltage	$ V_{GS1} - V_{GS2} $	$V_{DG} = 20\ \text{V}$, $I_D = 200\ \mu\text{A}$		15	25	mV
Gate-Source Voltage Differential Change with Temperature	$\frac{\Delta V_{GS1} - V_{GS2} }{\Delta T}$	$V_{DG} = 20\ \text{V}$, $I_D = 200\ \mu\text{A}$ $T_A = -55\ \text{to}\ 125^\circ\text{C}$		20	100	$\mu\text{V}/^\circ\text{C}$
Saturation Drain Current Ratio	$\frac{I_{DSS1}}{I_{DSS2}}$	$V_{DS} = 20\ \text{V}$, $V_{GS} = 0\ \text{V}$	0.85	0.97	1	
Transconductance Ratio	$\frac{g_{fs1}}{g_{fs2}}$	$V_{DS} = 20\ \text{V}$, $I_D = 200\ \mu\text{A}$ $f = 1\ \text{kHz}$	0.85	0.97	1	
Differential Output Conductance	$ g_{os1} - g_{os2} $				0.1	
Differential Gate Current	$ I_{G1} - I_{G2} $	$V_{DG} = 20\ \text{V}$, $I_D = 200\ \mu\text{A}$ $T_A = 125^\circ\text{C}$		0.1	10	nA
Common Mode Rejection Ratio ^c	CMRR	$V_{DG} = 10\ \text{to}\ 20\ \text{V}$, $I_D = 200\ \mu\text{A}$		100		dB

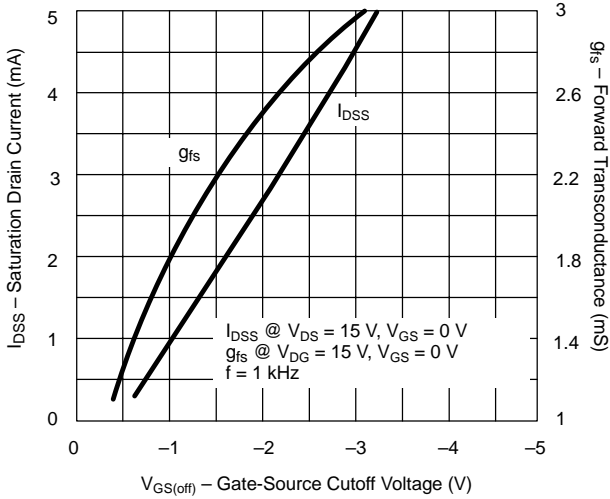
Notes

- a. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
 b. Pulse test: $PW \leq 300\ \mu\text{s}$ duty cycle $\leq 3\%$.
 c. This parameter not registered with JEDEC.

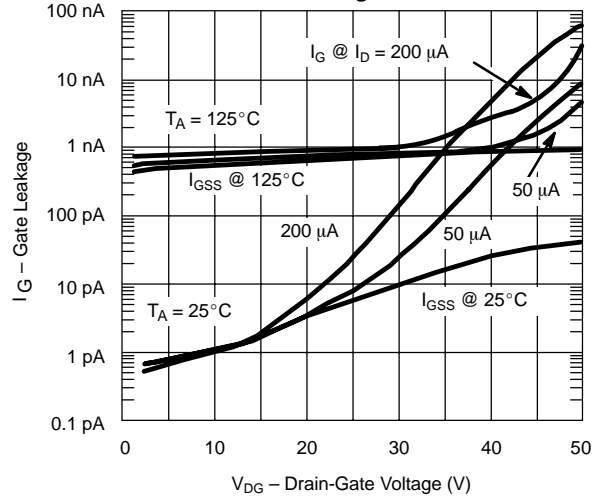
NQP

TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

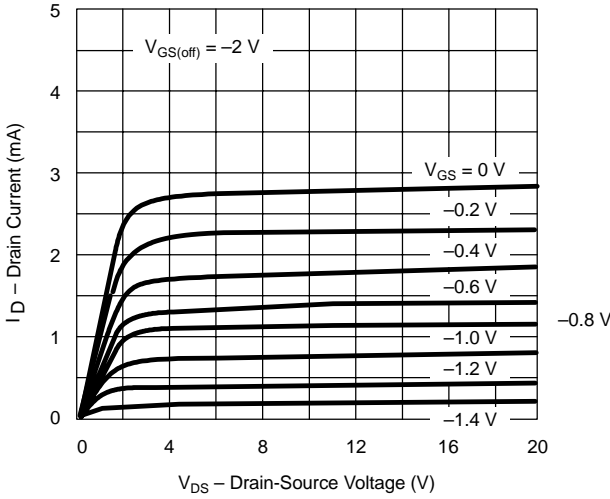
Drain Current and Transconductance vs. Gate-Source Cutoff Voltage



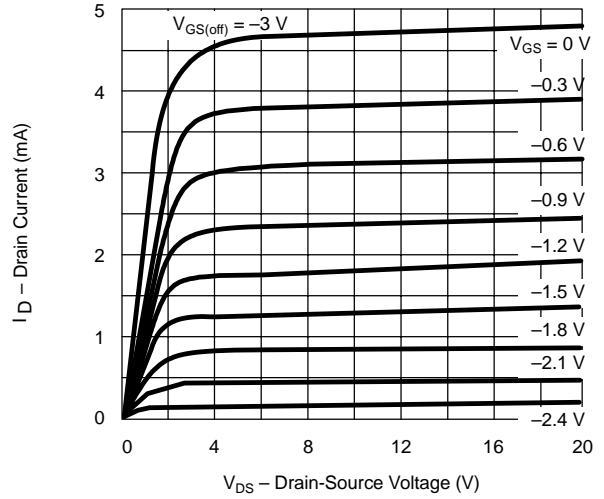
Gate Leakage Current



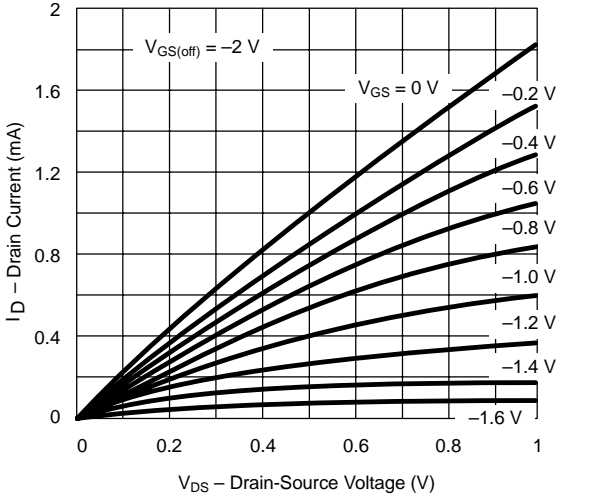
Output Characteristics



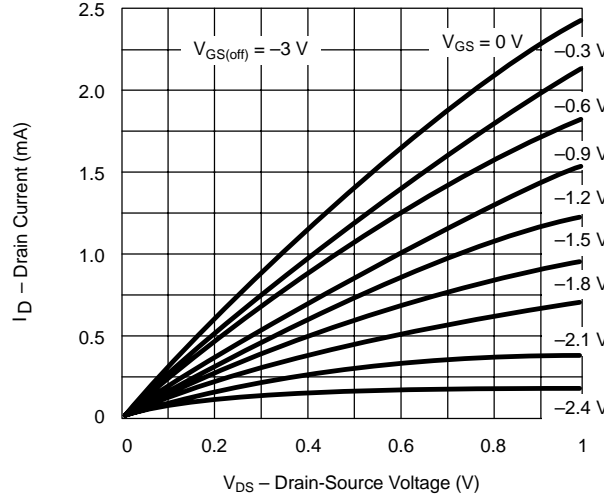
Output Characteristics



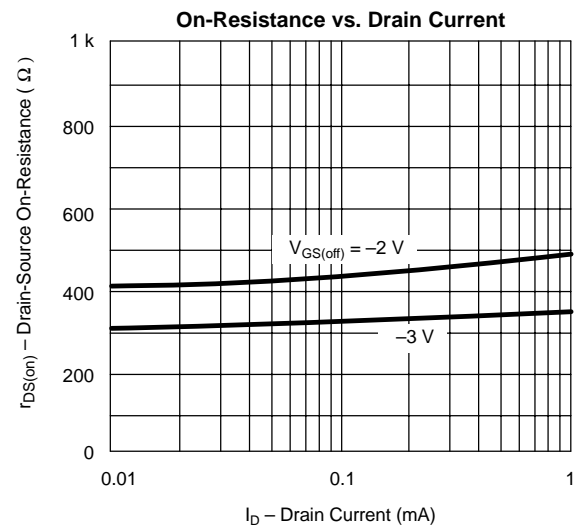
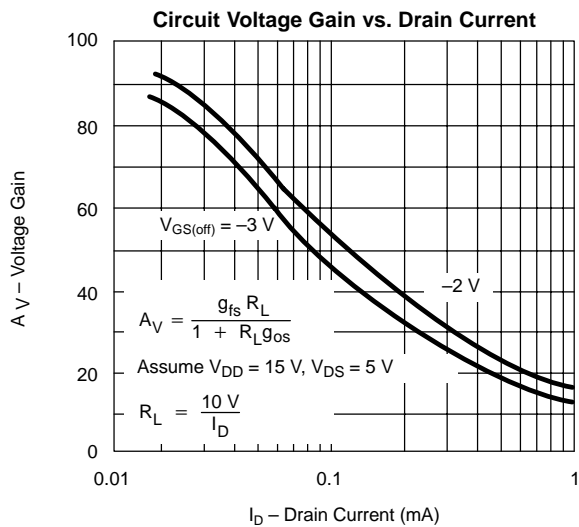
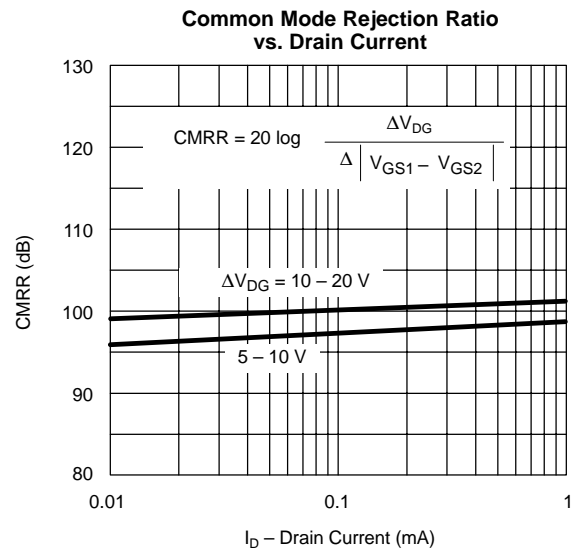
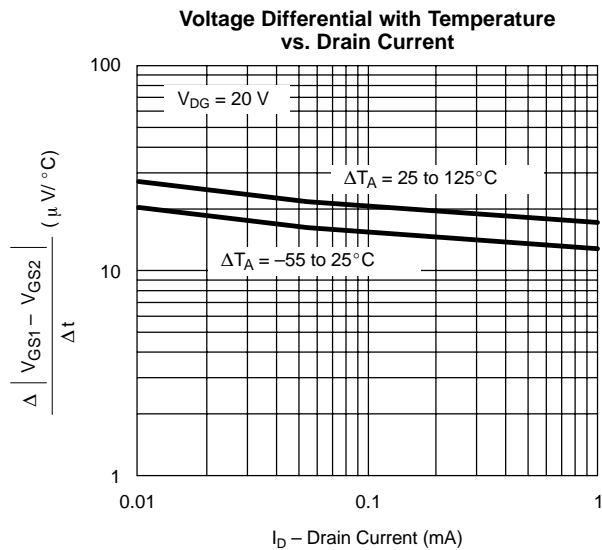
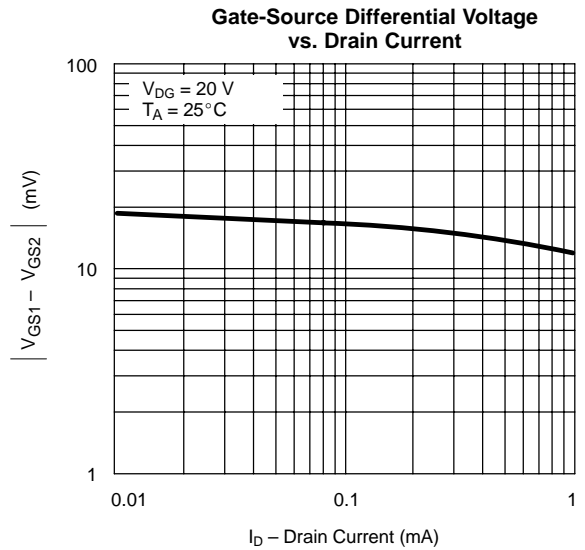
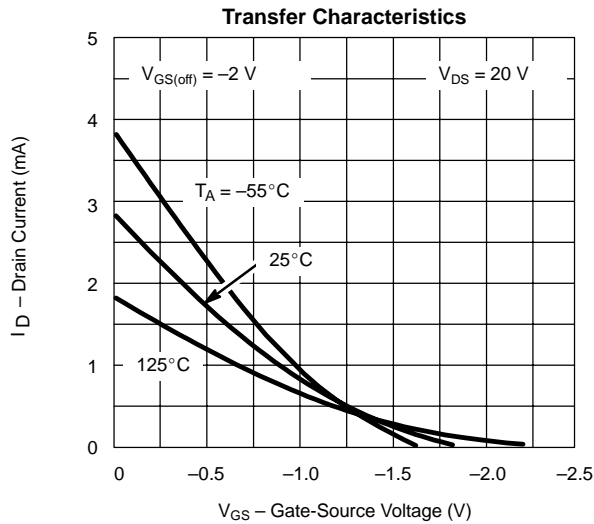
Output Characteristics



Output Characteristics



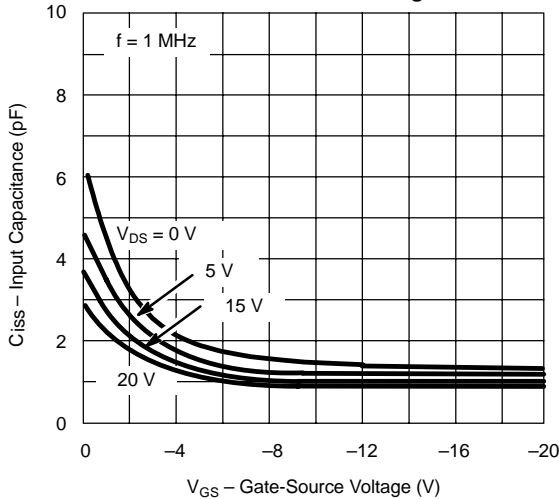
TYPICAL CHARACTERISTICS (T_A = 25°C UNLESS OTHERWISE NOTED)



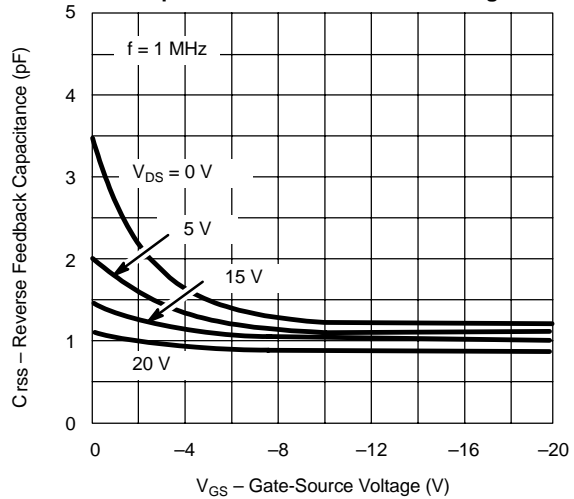


TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

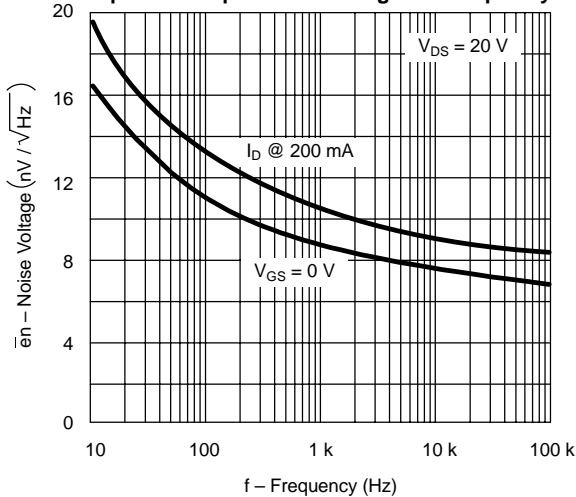
Common-Source Input Capacitance vs. Gate-Source Voltage



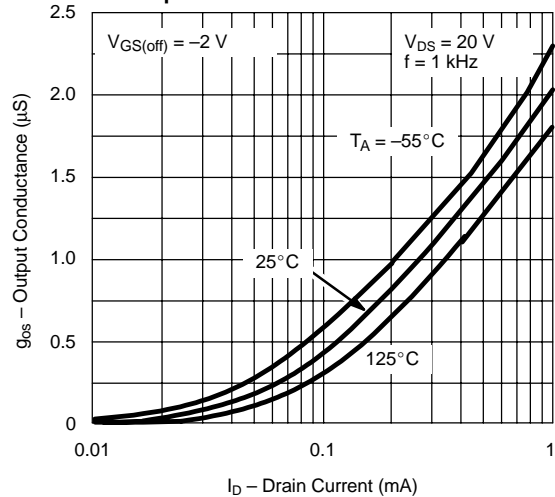
Common-Source Reverse Feedback Capacitance vs. Gate-Source Voltage



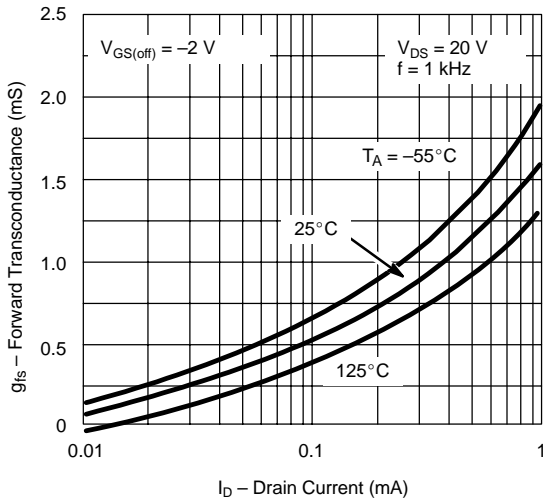
Equivalent Input Noise Voltage vs. Frequency



Output Conductance vs. Drain Current



Common-Source Forward Transconductance vs. Drain Current



On-Resistance and Output Conductance vs. Gate-Source Cutoff Voltage

